

Claims

1. A semiconductor device, comprising:
 - a stacked body including a first electrode layer, a second electrode layer provided to be electrically insulated from the first electrode layer in a stacking direction, and a third electrode layer provided to be electrically insulated from the second electrode layer in the stacking direction;
 - at least two first insulating layers provided in the stacked body to range from an upper end of the stacked body to a lower end of the stacked body, and extending in a first direction intersecting the stacking direction;
 - a first staircase portion provided in a first end region of the stacked body between the at least two first insulating layers;
 - a second staircase portion provided in a second end region of the stacked body located on a side opposite to the first end region between the at least two first insulating layers;
 - a second insulating layer extending in the first direction, the second insulating layer provided in the stacked body between the at least two first insulating layers, and dividing the second electrode layer and the third electrode layer in the first direction;
 - and
 - an interconnection electrically connecting the second electrode layer and the third electrode layer in the stacked body.
2. The device according to claim 1, wherein
 - the first electrode layer is a word line,
 - the second electrode layer is a first selection gate layer, and
 - the third electrode layer is a second selection gate layer.
3. The device according to claim 2, wherein the word line is a

dummy word line.

4. The device according to claim 1, wherein
the stacked body includes a first column-shaped portion provided in an intermediate region of the stacked body located between the first end region and the second end region, the first column-shaped portion extending in the stacking direction, and
the first column-shaped portion includes:
 - a semiconductor body extending in the stacking direction; and
 - a charge storage portion provided between the semiconductor body and the first electrode layer.
5. The device according to claim 1, wherein
the interconnection is provided in the stacked body, and
the interconnection is provided along the second insulating layer.
6. The device according to claim 1, further comprising a third insulating layer extending in the first direction, the third insulating layer provided in the stacked body between the first insulating layer and the second insulating layer, and dividing the second electrode layer and the third electrode layer in the first direction.